

Applicant : Rainer Butendeich et al.  
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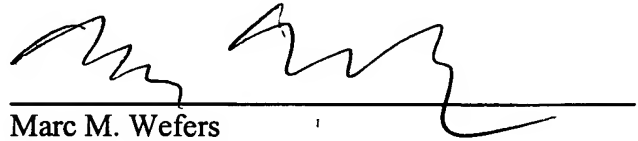
REMARKS

Attached to this Reply is an abstract showing the desired changes and a separate clean copy of the abstract incorporating the requested changes.

No fee is believed to be due at this time. Please apply any other charges or credits to deposit account 06-1050, referencing 12406-141US1.

Respectfully submitted,

Date: 07/26/06



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## ABSTRACT SHOWING CHANGES

### ~~Radiation-emitting semiconductor component~~

In a radiation-emitting semiconductor component with a layer structure comprising an n-doped confinement layer  $[(14)]$ , a p-doped confinement layer  $[(22)]$ , and an active, photon-emitting layer  $[(18)]$  disposed between the n-doped confinement layer  $[(14)]$  and the p-doped confinement layer  $[(22)]$ , it is provided according to the invention that the n-doped confinement layer  $[(14)]$  is doped with a first n-dopant (or two mutually different n-dopants) for producing high active doping and a sharp doping profile, and the active layer  $[(18)]$  is doped with only one second n-dopant, different from the first dopant, for improving the layer quality of the active layer  $[(18)]$ .

### ~~Figure 1~~